



C. Material Growth & Characterization 분과

2019년 2월 14일(목), 11:00-12:45

Room G (루비3, 5층)

[TG2-C] III-V & Materials Growth/Calculations

좌장: 박일규 교수(서울과학기술대학교), 송정훈 교수(공주대학교)

TG2-C-1 11:00-11:15	A Production Method in Heavily-Doped Silicon Wafer for Power Device Do-Won Song, Moon-Ju Bae, and Kye-Jung Chae <i>Growing Tech. Development Team, Development & Manufacturing Division, SK Siltron</i>
TG2-C-2 11:15-11:45	[초청] Designing Epitaxial Mixed Metal Oxide Films for Advantageous Functionalities Seungho Cho <i>School of Materials Science and Engineering, UNIST</i>
TG2-C-3 11:45-12:00	Suppression of Phase Separation of InAlAs Epitaxial Layers Grown on InP (001) Substrate Using MOCVD In-Situ Impurity Doping Method Hyunchul Jang ^{1,2} , Kwangwook Park ¹ , Hyong-Ho Park ¹ , Sang Hyun Jung ¹ , In-Guen Lee ^{1,2} , Dae-Hong Ko ² , and Chan-Soo Shin ¹ <i>¹KANC, ²Department of Material Science and Engineering, Yonsei University</i>
TG2-C-4 12:00-12:15	Effect of the Two-Dimensional Strain on the Equilibrium Crystal Shape of GaAs by Ab-initio Thermodynamics In Won Yeu ^{1,2,3} , Gyuseung Han ^{1,2,3} , Cheol Seong Hwang ^{2,3} , and Jung-Hae Choi ¹ <i>¹Center for Electronic Materials, KIST, ²Department of Materials Science and Engineering, Seoul National University, ³Inter-University Semiconductor Research Center, Seoul National University</i>
TG2-C-5 12:15-12:30	Phase Diagram of Ga(As,Sb) and (In,Ga)As by Cluster Expansion and DFT Calculations Gyuseung Han ^{1,2,3} , In Won Yeu ^{1,2,3} , Seung Cheol Lee ⁴ , Cheol Seong Hwang ¹ , and Jung-Hae Choi ^{2,3} <i>¹Center for Electronic Materials, KIST, ²Department of Materials Science and Engineering, Seoul National University, ³Inter-University Semiconductor Research Center, Seoul National University, ⁴Indo-Korea Science and Technology Center, India</i>
TG2-C-6 12:30-12:45	GaAs Laser Diodes Directly Grown on Si (001) Substrate 한원석, 고영호, 김갑중, 김덕준, 백주희, 전수경, 허영미, 김종희 <i>한국전자통신연구원 광통신부품연구그룹</i>